

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	358552	substrate.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:36
L2	2160	1 and piezo\$8 near3 (layer film coating thin sheet).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:36
L3	400	2 and insulat\$5 near3 (layer film coating thin sheet).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 15:37
L4	147	3 and conduct\$5 near3 (layer film coating thin sheet).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:26
L5	21	4 and (arsenide aluminium gallium mendeleeev).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:16
L6	28	4 and contact\$5 near3 (layer film coating thin sheet).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:16
L7	15	6 and (arsenide aluminium gallium mendeleeev)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 17:10
L8	9	4 and piezo\$8 near4 semiconductor. clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 16:27

L9	2	4 and (arsenide near3 aluminium near3 gallium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/21 17:22
L10	2	("4965697").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 17:22